

# FDS3680 100V N-Channel PowerTrench<sup>®</sup> MOSFET

# General Description

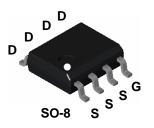
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

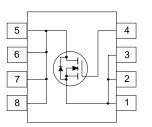
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{\text{DS}(\text{ON})}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

### Features

- 5.2 A, 100 V.  $R_{DS(ON)} = 0.043 \ \Omega \ @ V_{GS} = 10 \ V$  $R_{DS(ON)} = 0.048 \ \Omega \ @ V_{GS} = 6 \ V.$
- Low gate charge.
- Fast switching speed
- High performance trench technology for extremely low  $R_{\text{DS}(\text{ON})}$  .
- High power and current handling capability.





### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		100	V
V <sub>GSS</sub>	Gate-Source Voltage		±20	V
ID	Drain Current – Continuous	(Note 1a)	5.2	A
	- Pulsed		50	
PD	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
TJ, TSTG	Operating and Storage Junction Temperature Range		-55 to +150	°C

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

## Package Marking and Ordering Information

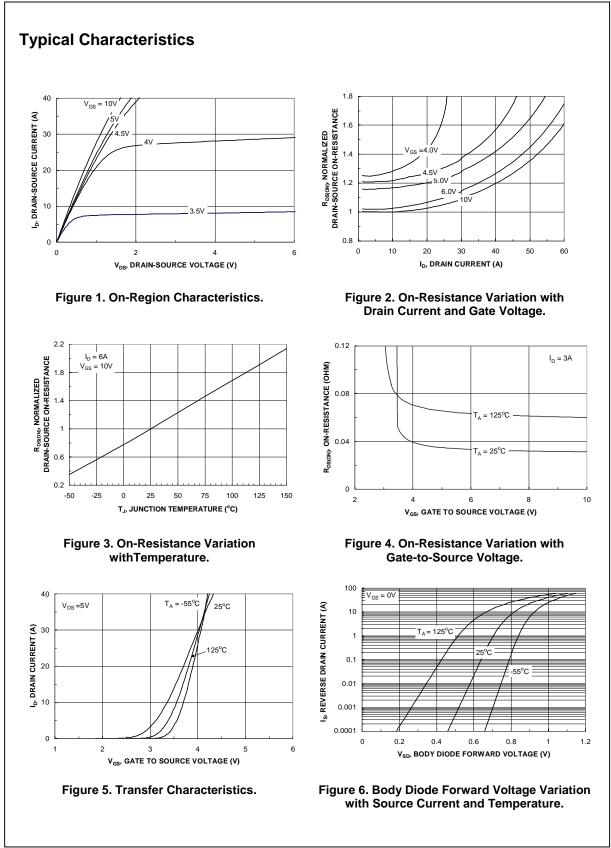
EDS3680 EDS3680 13" 12mm	Device Marking	Device	Reel Size	Tape width	Quantity
	FDS3680	FDS3680	13"	12mm	2500 units

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FDS3680

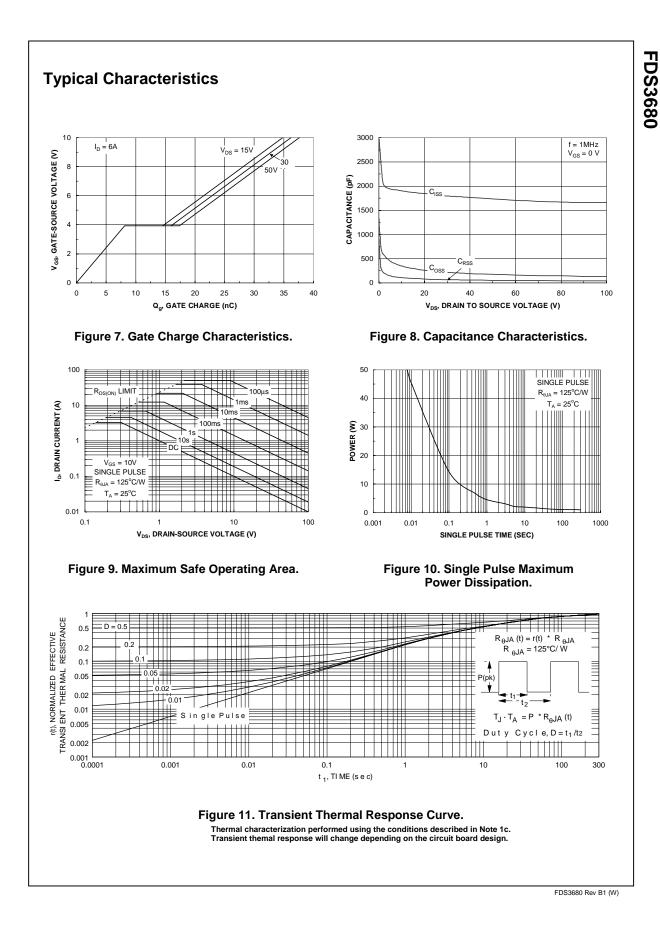
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	100			V
<u>ΔBVdss</u> ΔTj	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		101		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			25	μA
I <sub>GSSF</sub>	Gate–Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate–Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V} \qquad V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	2	2.4	4	V
$rac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		-6.5		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = 10 V,$ $I_D = 5.2 A$ $V_{GS} = 10 V,$ $I_D = 5.2 A$ $T_J=125^{\circ}C$ $V_{GS} = 6 V,$ $I_D = 4.5 A$		0.032 0.061 0.034	0.043 0.086 0.048	Ω
I <sub>D(on)</sub>	On–State Drain Current	$V_{GS} = 6 V, \qquad I_D = 4.5 A$ $V_{GS} = 10 V, \qquad V_{DS} = 5 V$	25	0.001	0.010	А
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 V$ , $I_D = 5.2 A$		25		S
Dunomio	Characteristics					
	Characteristics	$V_{DS} = 50 V$ , $V_{GS} = 0 V$ ,	1	1735	1	pF
	Output Capacitance	f = 1.0  MHz		176	}	pF
	Reverse Transfer Capacitance	_		53	<u> </u>	pF
	·			00		Р
	Turn–On Delay Time	$V_{DD} = 50 \text{ V}, \qquad I_D = 1 \text{ A},$		14	25	ns
t <sub>a(on)</sub>	Turn–On Rise Time	$V_{GS} = 10 \text{ V},  R_{GEN} = 10 \Omega$		8.5	17	ns
t <sub>d(off)</sub>	Turn–Off Delay Time			63	94	ns
t <sub>f</sub>	Turn-Off Fall Time	_		21	34	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 50 \text{ V}, \qquad I_D = 6 \text{ A},$		38	53	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = 10 V$		8.1	00	nC
Q <sub>gd</sub>	Gate-Drain Charge	_		9.2		nC
	Ũ	and Marine Patiens		-		_
	ource Diode Characteristics				21	Δ
V <sub>SD</sub>	Drain–Source Diode Forward	$V_{GS} = 0 \text{ V},  I_S = 2.1 \text{ A}  (\text{Note 2})$		0.73	1.2	V
otes: R <sub>θJA</sub> is the sun	Maximum Continuous Drain–Source Drain–Source Diode Forward Voltage nof the junction-to-case and case-to-ambient ther R <sub>eJC</sub> is guaranteed by design while R <sub>eCA</sub> is detern a) 50°C/W when mounted on a 1in <sup>2</sup> pad of 2 oz copper	$V_{GS}=0\ V,  I_S=2.1\ A \qquad (\text{Note 2})$ mal resistance where the case thermal reference	рю I с)	as the solde	er mounting when moun	

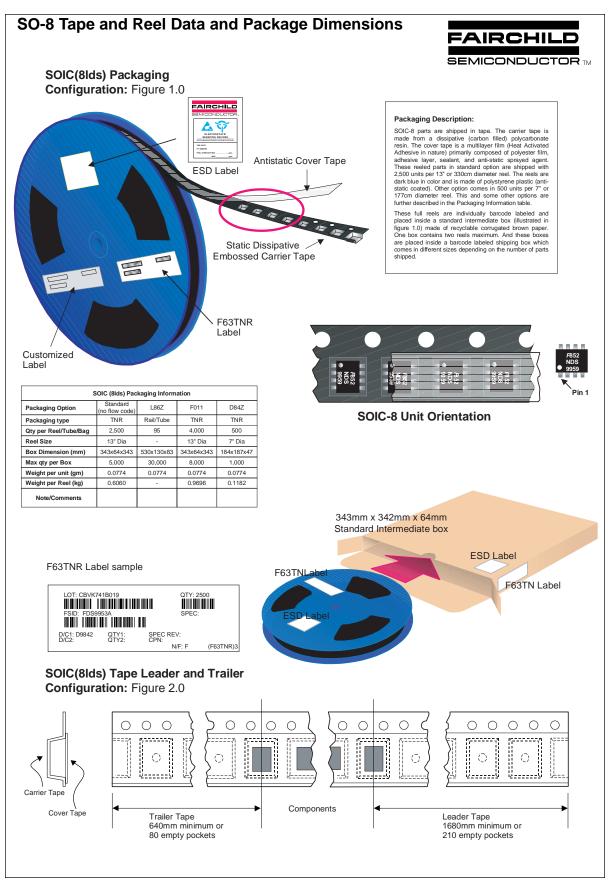
FDS3680 Rev B1 (W)



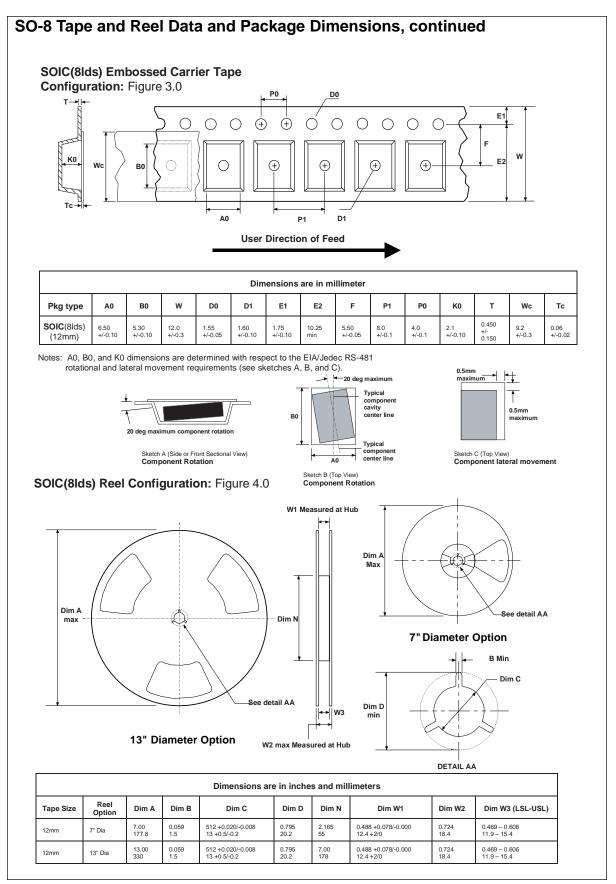
FDS3680 Rev B1 (W)

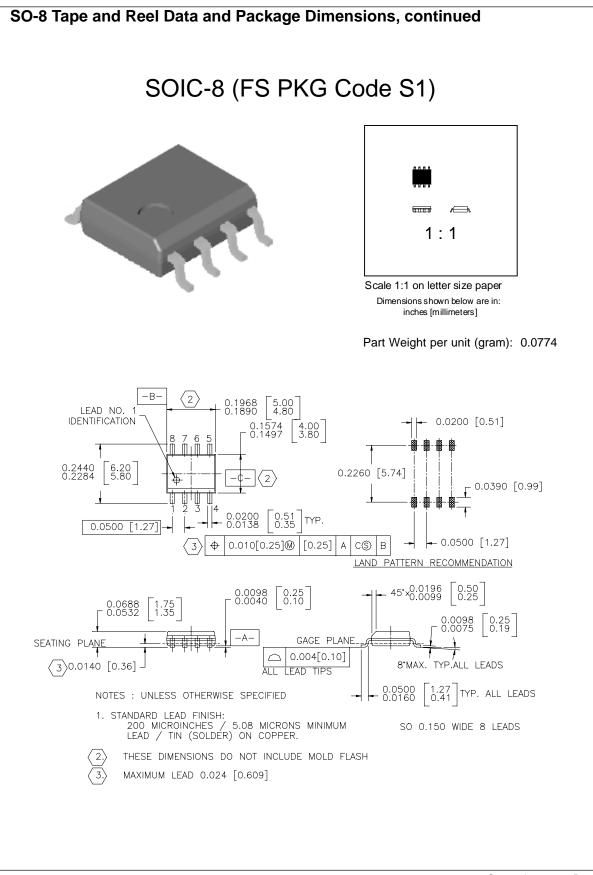
FDS3680





July 1999, Rev. B





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